

BD239/A/B/C

Medium Power Linear and Switching Applications

Complement to BD240/A/B/C respectively



NPN Epitaxial Silicon Transistor

1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings T_C=25°C unless otherwise noted

<u> </u>		
Parameter	Value	Units
Collector-Emitter Voltage	MAL.	
: BD239	45	V
: BD239A	60	V
: BD239B	80	V
: BD239C	100	V
Collector-Emitter Voltage		
: BD239	55	V
: BD239A	70	V
: BD239B	90	V
: BD239C	115	V
Emitter-Base Voltage	5	V
Collector Current (DC)	2	A CO
*Collector Current (Pulse)	4	Α
Base Current	0.6	А
Collector Dissipation (T _C =25°C)	30	W
Junction Temperature	150	°C
Storage Temperature	- 65 ~ 150	°C
	Collector-Emitter Voltage : BD239 : BD239A : BD239B : BD239C Collector-Emitter Voltage : BD239 : BD239A : BD239A : BD239A : BD239B : BD239B : BD239C Emitter-Base Voltage Collector Current (DC) *Collector Current (Pulse) Base Current Collector Dissipation (T _C =25°C) Junction Temperature	Collector-Emitter Voltage : BD239 45 : BD239A 60 : BD239B 80 : BD239C 100 Collector-Emitter Voltage : BD239 55 : BD239A 70 : BD239B 90 : BD239C 115 Emitter-Base Voltage 5 Collector Current (DC) 2 *Collector Current (Pulse) 4 Base Current 0.6 Collector Dissipation (T _C =25°C) 30 Junction Temperature 150

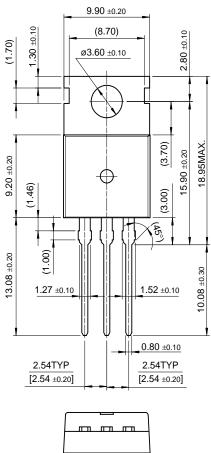
Electrical Characteristics T_C=25°C unless otherwise noted

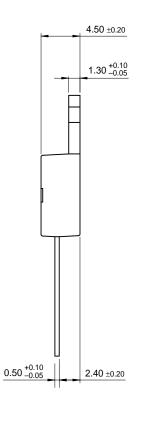
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	*Collector-Emitter Sustaining Voltage : BD239 : BD239A : BD239B : BD239C	I _C = 30mA, I _B = 0	45 60 80 100	担于	市	V V V
I _{CEO}	Collector Cut-off Current	ATT. 1		ALTO.		
	: BD239/A	$V_{CE} = 30V, I_{B} = 0$			0.3	mA
	: BD239B/C	$V_{CE} = 60 \text{ V}, I_{B} = 0$			0.3	mA
I _{CES}	Collector Cut-off Current					
	: BD239	$V_{CF} = 45V, V_{BF} = 0$			0.2	mA
	: BD239A	$V_{CF} = 60V, V_{BF} = 0$			0.2	mA
	: BD239B	$V_{CF} = 80V, V_{BF} = 0$			0.2	mA
	: BD239C	$V_{CE} = 100V, V_{BE} = 0$			0.2	mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			1	mA
h _{FE}	*DC Current Gain	$V_{CF} = 4V, I_{C} = 0.2A$	40			
		$V_{CE} = 4V, I_{C} = 1A$	15			
V _{CE} (sat)	*Collector-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.2A$			0.7	V
V _{BE} (on)	*Base-Emitter ON Voltage	$V_{CE} = 4V$, $I_{C} = 1A$			1.3	V

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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